

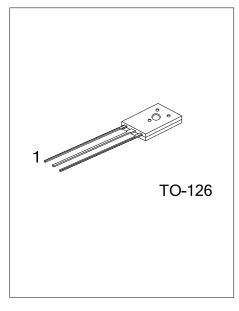
BD139A

NPN SILICON TRANSISTOR

NPN POWER TRANSISTORS

FEATURES

- * High current (max.1.5A)
- * Low voltage (max.80V)



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Deelving	
Lead Free	Lead Free Halogen Free		1	2	3	Packing	
BD139AL-xx-T60-K	BD139AG-xx-T60-K	TO-126	ш	С	В	Bulk	
Note: Pin Assignment: E: Emitter C: Collector B: Base							
BD139AG-xx-AA3-R	 (1) K: Bulk (2) T60: TO-126 (3) refer to h_{FE} (4) G: Halogen Free and Lead Free, L: Lead Free 						

MARKING



■ ABSOLUTE MAXIMUM RATING

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	80	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current (DC)	lc	1.5	A
Peak Collector Current	I _{CM}	2	A
Peak Base Current	I _{BM}	1	А
Power Dissipation (T _A =25°C)	PD	1.25	W
Junction Temperature	TJ	+150	°C
Operating Temperature	T _{OPR}	-65 ~ +150	°C
Storage Temperature	T _{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ _{JA}	100	°C/W
Junction to Case	θ _{JC}	10	°C/W

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Collector Cut-Off Current		lana	I _E =0, V _{CB} =30V				100	nA
		ICBO	I _E =0, V _{CB} =30V, T _J =125°C				10	μA
Emitter Cut-Off Current		I _{EBO}	I _C =0, V _{EB} =5V				100	nA
DC Current Gain		h _{FE}	V _{CE} =2V	I _C =5mA	40			
				I _C =150mA	63		250	
				I _C =500mA	25			
DC Current Gain	BD139A-16		I _C =150mA, V _{CE} =2V		100		250	
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	I _C =500mA, I _B =50mA				0.5	V
Base-Emitter Voltage		V _{BE}	I _C =500mA, V _{CE} =2V				1	V
Transition Frequency		f⊤	I _C =500mA, V _{CE} =5V,		190		MHz	

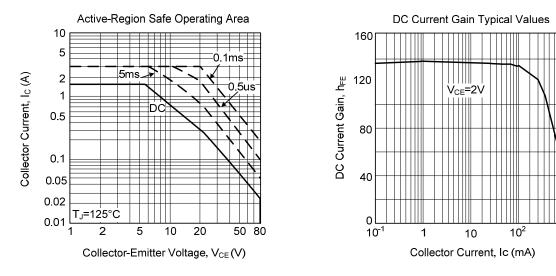


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TYPICAL CHARACTERISTICS



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